

150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor
19 November 2015 Product data sheet

1. General description

PNP high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBHV8515QA.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C
- Low package height of 0.37 mm
- AEC-Q101 qualified
- Suitable for Automatic Optical Inspection (AOI) of solder joint

3. Applications

- LED driver for LED chain module
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-150	V
I _C	collector current		-	-	-500	mA
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	200	-	



150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	Е	emitter		В
3	С	collector	4 3	'*_
4	С	collector	2	sym132
			Transparent top view DFN1010D-3 (SOT1215)	

6. Ordering information

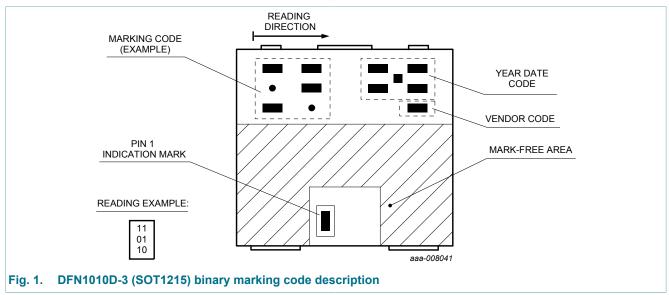
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV9515QA	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9515QA	00 01 11



PBHV9515QA

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150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-150	V
V_{CEO}	collector-emitter voltage	open base		-	-150	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			_	-500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	Α
I _{BM}	peak base current			-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			<u>[5]</u>	-	1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

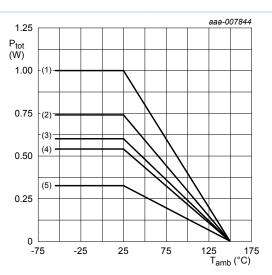
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

^[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 6 cm²
- (3) FR4 PCB, single-sided copper, 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
ambient	ambient		<u>[3]</u>	-	-	169	K/W
			[4]	-	-	232	K/W
			<u>[5]</u>	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

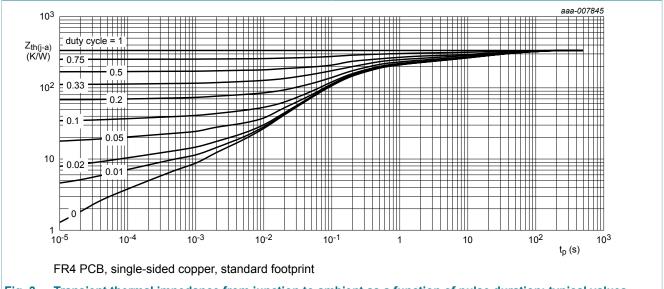


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

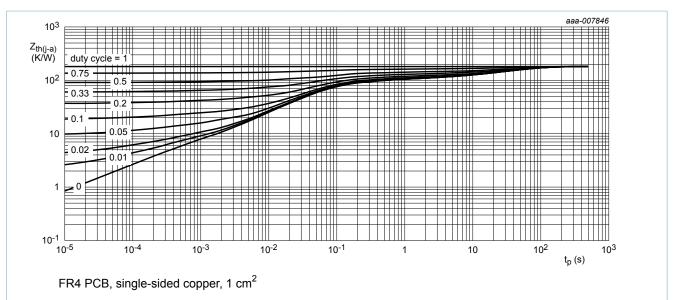
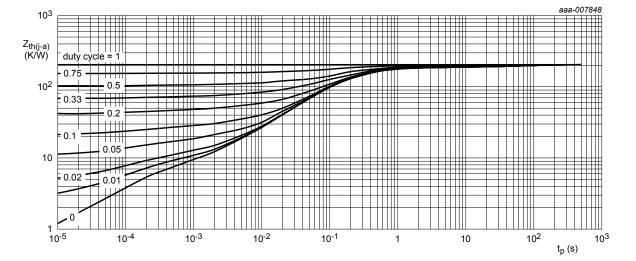


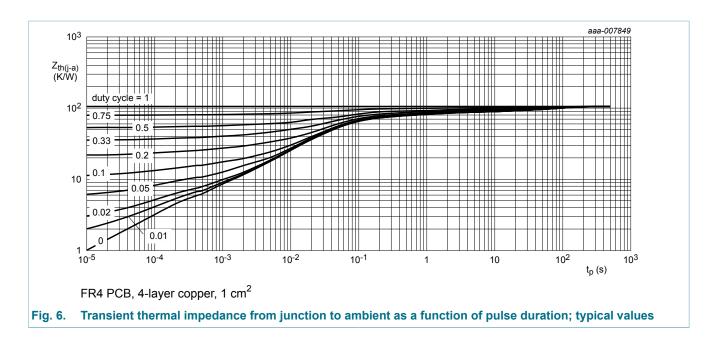
Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor



7/17

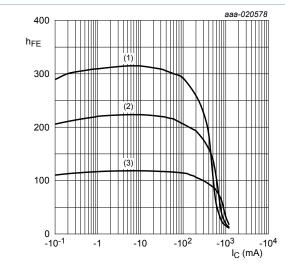
150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -120 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μΑ
ces	collector-emitter cut-off current	V _{CE} = -120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{ЕВО}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE} DC	DC current gain	V_{CE} = -10 V; I_{C} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	210	-	
		V_{CE} = -10 V; I_{C} = -100 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02; T_{amb} = 25 ^{\circ}C$	100	200	-	
		V_{CE} = -10 V; I_{C} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	190	-	
		V_{CE} = -10 V; I_{C} = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	70	135	-	
02001	collector-emitter	I_{C} = -50 mA; I_{B} = -5 mA; T_{amb} = 25 °C	-	-65	-110	mV
	saturation voltage	I_{C} = -100 mA; I_{B} = -10 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-80	-140	mV
		I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-60	-110	mV
		I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-90	-160	mV
		I_C = -500 mA; I_B = -100 mA; pulsed;	-	-180	-300	mV
V_{BEsat}	base-emitter saturation voltage	$t_p \le 300 \text{ μs; } δ \le 0.02; T_{amb} = 25 \text{ °C}$	-	-0.95	-1.2	V
d	delay time	V _{CC} = -10 V; I _C = -100 mA;	-	14	-	ns
·Г	rise time	I _{Bon} = -20 mA; I _{Boff} = 20 mA;	-	46	-	ns
ton	turn-on time	T _{amb} = 25 °C	-	60	-	ns
t _s	storage time		-	455	-	ns
f	fall time		-	105	-	ns
off	turn-off time		-	560	-	ns
fт	transition frequency	V_{CE} = -10 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	-	75	-	MHz
C _c	collector capacitance	V _{CB} = -20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	4.7	-	pF

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = 0 \text{ A}; i_C = 0 \text{ A};$	-	90	-	pF
		f = 1 MHz; T _{amb} = 25 °C				



 V_{CE} = -10 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 7. DC current gain as a function of collector current; typical values

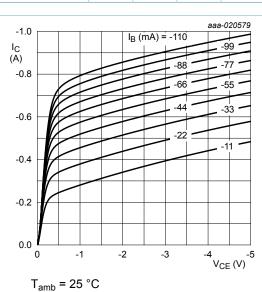
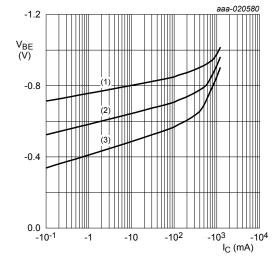


Fig. 8. Collector current as a function of collectoremitter voltage; typical values



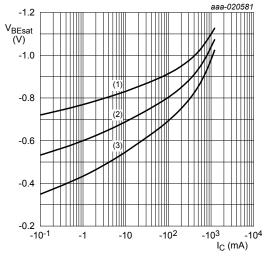
 V_{CE} = -10 V

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 9. Base-emitter voltage as a function of collector current; typical values



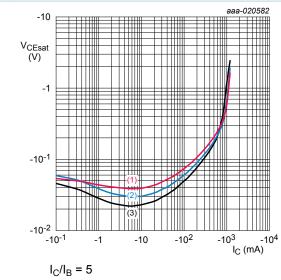
$$I_C/I_B = 5$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
= 100 °C

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

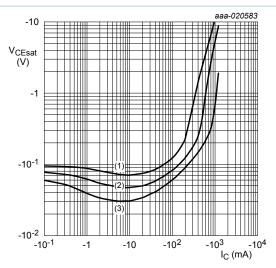


(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



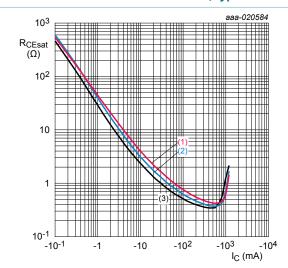
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



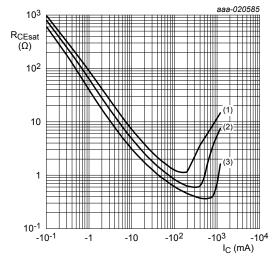
$$I_C/I_B = 5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

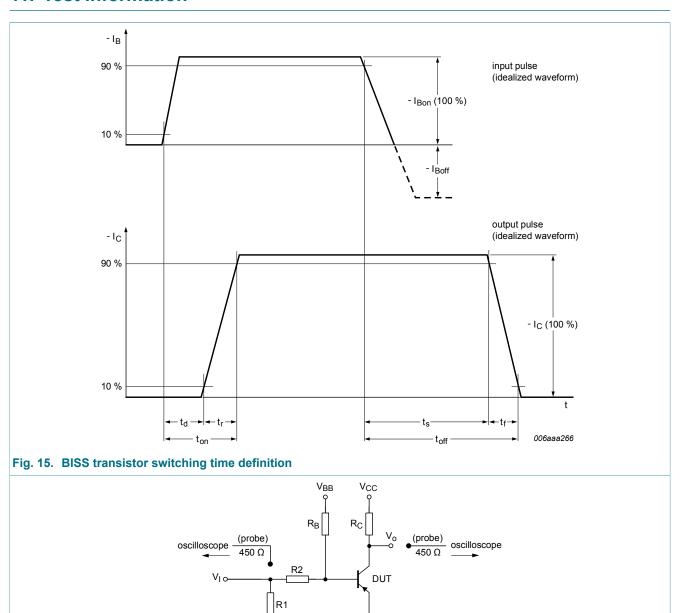
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

11. Test information



11.1 Quality information

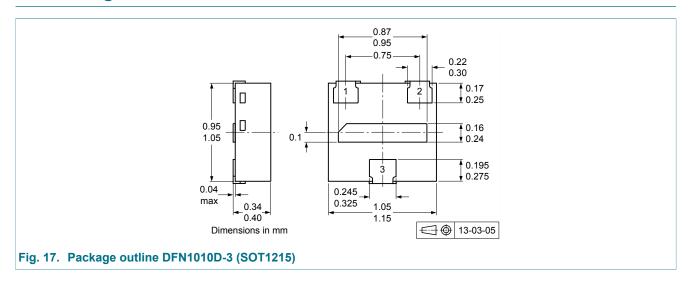
Fig. 16. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

mgd624

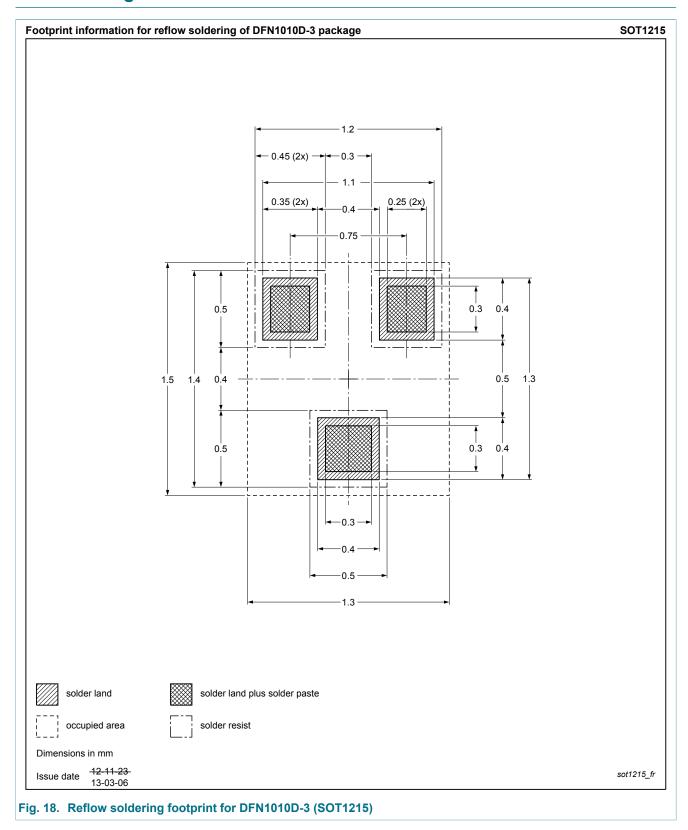
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12. Package outline



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13. Soldering



PBHV9515QA

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9515QA v.1	20151119	Product data sheet	-	-

150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	5
10	Characteristics	8
11	Test information	11
11.1	Quality information	11
12	Package outline	12
13	Soldering	13
14	Revision history	14
15	Legal information	15
15.1	Data sheet status	15
15.2	Definitions	15
15.3	Disclaimers	15
15.4	Trademarks	16

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